## What is claimed is:

- 1 1. An electrochemical deposition system comprising:
- 2 a housing;
- a plating system disposed within the housing;
- a remediation module disposed within the housing; and
- a substrate transfer system disposed within the housing and adapted to transfer a
- 6 substrate directly from the remediation module to the plating system.
- 1 2. The system of claim 1, wherein the plating system comprises a plating chamber
- 2 disposed within the housing, having a plating bath within.
- 1 3. The system of claim 1, wherein the plating system comprises a plating bath disposed
- 2 within the housing.
- 1 4. The system of claim 1, wherein the substrate transfer system comprises a robotic
- 2 handling system.
- 1 5. The system of claim 1, wherein the substrate transfer system comprises a single
- 2 device instance.
- 1 6. The system of claim 1, wherein the substrate transfer system comprises multiple
- 2 device instances.

- 1 7. The system of claim 1, wherein the remediation module comprises a dedicated
- 2 treatment system.
- 1 8. The system of claim 7, wherein the treatment system comprises a reactive plasma
- 2 system.
- 1 9. The system of claim 8, wherein the reactive plasma system comprises hydrogen
- 2 plasma.
- 1 10. The system of claim 8, wherein the reactive plasma system comprises oxygen plasma.
- 1 11. The system of claim 7, wherein the treatment system comprises a non-plasma reactive
- 2 environment system.
- 1 12. The system of claim 11, wherein the non-plasma reactive environment system
- 2 comprises an ultraviolet ozone remediation system.
- 1 13. A device for performing electrochemical deposition of copper on a substrate having a
- 2 copper seed layer, the device comprising:
- 3 a housing;

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- a copper plating bath disposed within the housing;
- a seed layer treatment system, disposed within the housing, comprising a reactive
- 6 environment medium; and
- a substrate transfer system disposed within the housing and adapted to transfer the

- 8 substrate directly and immediately from the reactive environment medium to the copper
- 9 plating bath.
- 1 14. The device of claim 13, wherein the reactive environment system comprises a
- 2 reactive plasma system.
- 1 15. The device of claim 14, wherein the reactive plasma system comprises hydrogen
- 2 plasma.
- 1 16. The device of claim 14, wherein the reactive plasma system comprises oxygen
- 2 plasma.
- 1 17. The device of claim 13, wherein the reactive environment system comprises a non-
- 2 plasma reactive environment system.
- 1 18. A method of depositing copper upon a semiconductor substrate, comprising the steps
- 2 of:
- providing a substrate having a copper seed layer formed thereon;
- 4 exposing the substrate to a reactive environment treatment adapted to remove
- 5 contaminants from an exposed surface of the copper seed layer;
- 6 immediately transferring the substrate from the reactive environment treatment to a
- 7 copper plating bath; and
- 8 plating copper onto the copper seed layer utilizing the copper plating bath;
- 9 wherein the steps of exposing the substrate to a reactive environment treatment,
- 10 immediately transferring the substrate, and plating copper onto the copper seed layer are

- performed within a single apparatus.
- 1 19. The method of claim 18, wherein the reactive environment treatment comprises a
- 2 reactive plasma system.
- 1 20. The method of claim 18, wherein the reactive environment treatment comprises a
- 2 non-plasma reactive environment system.
- 1 21. A method of removing surface contaminants from a copper seed layer disposed upon
- 2 a semiconductor substrate in preparation for electrochemical deposition, comprising the steps
- 3 of:
- 4 providing an electrochemical deposition apparatus having a contaminant remediation
- 5 module housed within;
- transferring the semiconductor substrate into the remediation module;
- y using the remediation module to remove contaminants from the surface of the copper
- 8 seed layer; and
- 9 immediately transferring the semiconductor substrate from the remediation module
- into a plating system also housed within the electrochemical deposition apparatus.